NCE N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The NCE0160S uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

GENERAL FEATURES

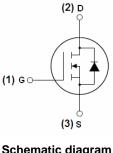
- $V_{DS} = 100V, I_{D} = 60A$ $R_{DS(ON)}$ <14m Ω @ V_{GS} =10V
- Special designed for Convertors and power controls
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin Assignment



PowerPAK SO-8 Bottom view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0160	NCE0160S	PowerPAK SO-8	-	-	-

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

– ,	•		
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±25	V
Drain Current-Continuous	I _D	60	Α
Drain Current-Continuous(T _C =70°C)	I _D (70℃)	50	А
Pulsed Drain Current	I _{DM}	80	А
Maximum Power Dissipation	P _D	105	W
Peak diode recovery voltage	dv/dt		V/ns
Derating factor		0.84	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	550	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	$^{\circ}$

NCE0160S

Thermal Characteristic

Thermal Resistance, Junction-to- Case (Note 2)	$R_{ heta Jc}$	1.19	°C/W	
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Electrical Characteristics (TA=25°C unless otherwise noted)

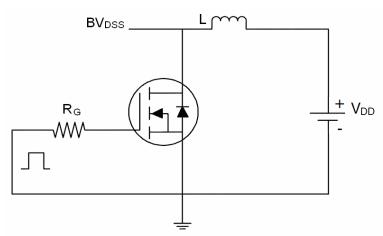
Zero Gate Voltage Drain Current Gate-Body Leakage Current On Characteristics (Note 3) Gate Threshold Voltage Drain-Source On-State Resistance Forward Transconductance Dynamic Characteristics (Note4) Input Capacitance IDSS V V GS(th) V SPS V CISS	/ _{GS} =0V I _D =250μA 100 / _{DS} =100V,V _{GS} =0V / _{GS} =±25V,V _{DS} =0V			V
Zero Gate Voltage Drain Current Gate-Body Leakage Current On Characteristics (Note 3) Gate Threshold Voltage Drain-Source On-State Resistance Forward Transconductance Dynamic Characteristics (Note4) Input Capacitance Output Capacitance Coss	_{DS} =100V,V _{GS} =0V			V
Gate-Body Leakage Current On Characteristics (Note 3) Gate Threshold Voltage Drain-Source On-State Resistance Forward Transconductance Dynamic Characteristics (Note4) Input Capacitance Output Capacitance Coss	, , , , , , , , , , , , , , , , , , , ,			•
On Characteristics (Note 3) Gate Threshold Voltage V _{GS(th)} V Drain-Source On-State Resistance R _{DS(ON)} V Forward Transconductance g _{FS} Dynamic Characteristics (Note4) Input Capacitance C _{Iss} Output Capacitance C _{oss}	_{'GS} =±25V,V _{DS} =0V		1	μA
			±100	nA
Drain-Source On-State Resistance R _{DS(ON)} Forward Transconductance g _{FS} Dynamic Characteristics (Note4) Input Capacitance C _{iss} Output Capacitance C _{oss}				
Forward Transconductance g _{FS} Dynamic Characteristics (Note4) Input Capacitance C _{lss} Output Capacitance C _{oss}	_{DS} =V _{GS} ,I _D =250μA 2.5	3.7	4.5	V
Dynamic Characteristics (Note4) Input Capacitance C _{lss} Output Capacitance C _{oss}	/ _{GS} =10V, I _D =30A		14	mΩ
Input Capacitance C _{iss} Output Capacitance C _{oss}	V _{DS} =15V,I _D =10A	30		S
Output Capacitance Coss	•			
Output Capacitance C _{oss}	(50)()(0)(2850		PF
Reverse Transfer Capacitance C _{rss}	/ _{DS} =50V,V _{GS} =0V,	220		PF
	F=1.0MHz	90		PF
Switching Characteristics (Note 4)				
Turn-on Delay Time t _{d(on)}		17		nS
Turn-on Rise Time t_r V_{DD}	=30V,I _D =5A,R _L =10Ω	10		nS
Turn-Off Delay Time t _{d(off)}	V_{GS} =10 V , R_G =1 Ω	26		nS
Turn-Off Fall Time t _f		10		nS
Total Gate Charge Q _g	/ 50)/1 404	47		nC
Gate-Source Charge Q _{gs}	/ _{DS} =50V,I _D =10A,	13		nC
Gate-Drain Charge Q _{gd}	V _{GS} =10V	12.5		nC
Drain-Source Diode Characteristics				
Diode Forward Voltage (Note 3) V _{SD}	V _{GS} =0V,I _S =4A		1.2	V
Diode Forward Current (Note 2)			60	Α
Reverse Recovery Time t _{rr} T.	TJ = 25°C, IF = 10A		60	nS
Reverse Recovery Charge Qrr di/o		1		
Forward Turn-On Time t _{on} Intrins	t = 100A/µs(Note3)		200	nC

Notes:

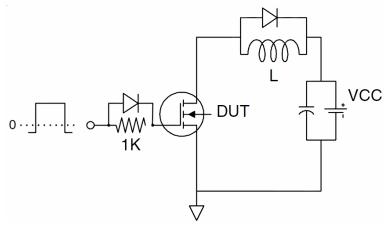
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

Test circuit

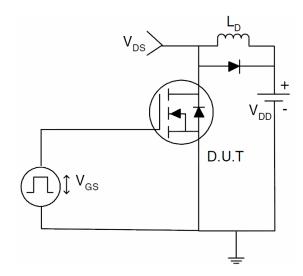
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

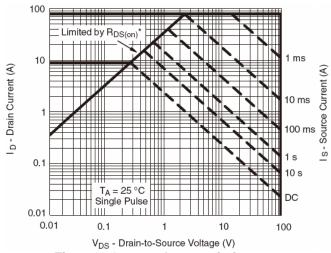
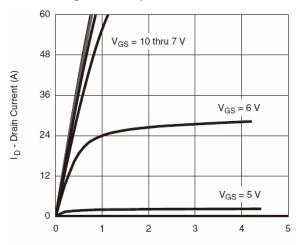


Figure3. Output characteristics



V_{DS} - Drain-to-Source Voltage (V) Figure5. Static drain-source on resistance

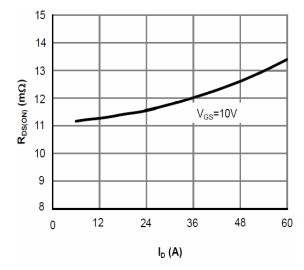


Figure 2. Source-Drain Diode Forward Voltage

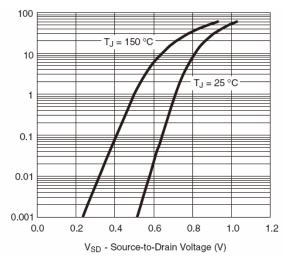


Figure 4. Transfer characteristics

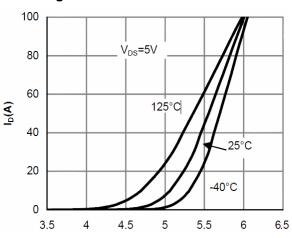
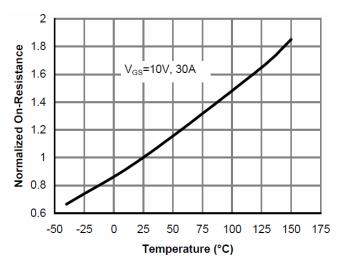
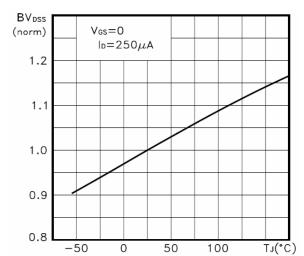
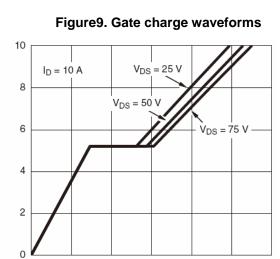


Figure 6. R_{DS(ON)} vs Junction Temperature









27

Q_q - Total Gate Charge (nC)

45

54

V_{GS} - Gate-to-Source Voltage (V)

Figure 8. V_{GS(th)} vs Junction Temperature

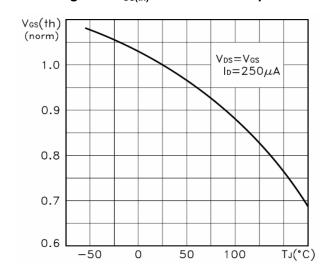
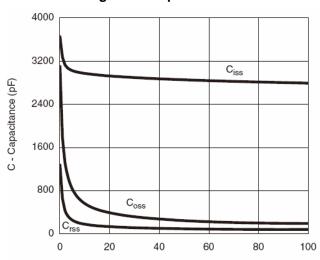
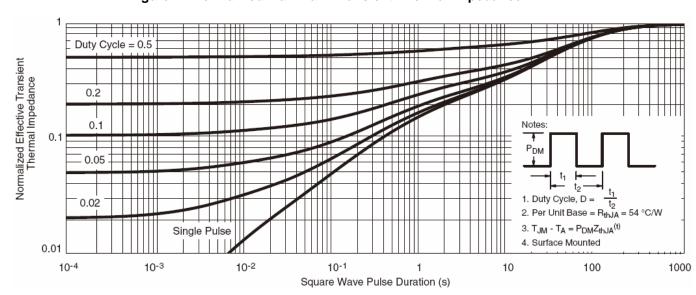


Figure 10. Capacitance



V_{DS} - Drain-to-Source Voltage (V)

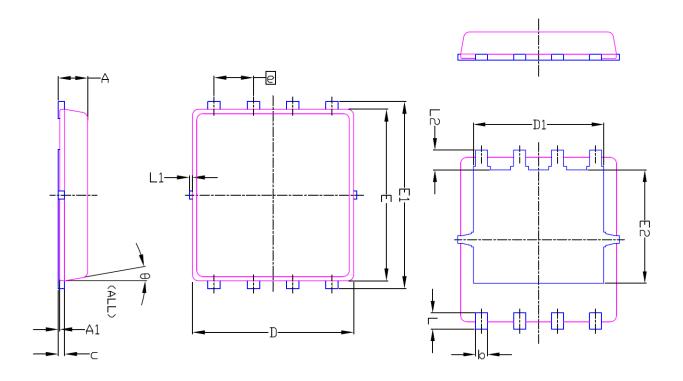
Figure11. Normalized Maximum Transient Thermal Impedance



Pb Free Product



PowerPAK SO-8 PACKAGE INFORMATION



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
2 I MBOL2	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0. 95	1.00	0. 033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1		4.35 BSC		0.171 BSC			
Е		5.55 BSC		0.219 BSC			
E1	E1 6. 05 BSC E2 3. 82 BSC			0. 238 BSC			
E2				0.150 BSC			
e	1.27 BSC			0.050 BSC			
L	0.45	0. 55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	

NCE0160S

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